

SANYO	No. 3819	<h1 style="margin: 0;">2SK1724</h1> <p style="margin: 0;">N-Channel MOS Silicon FET</p> <p style="margin: 0;">Very High-Speed Switching Applications</p>
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Features

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.

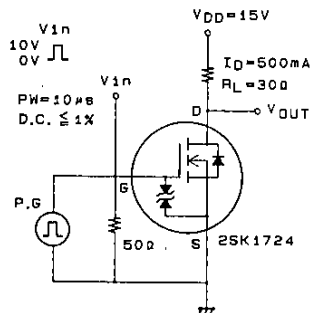
Absolute Maximum Ratings at Ta = 25°C

		unit
Drain to Source Voltage	V _{DSS}	30 V
Gate to Source Voltage	V _{GSS}	±15 V
Drain Current(DC)	I _D	1 A
Drain Current(Pulse)	I _{DP}	4 A
Allowable Power Dissipation	P _D	3.5 W
		Mounted on ceramic board (250mm ² × 0.8mm)
		1.3 W
Channel Temperature	T _{ch}	150 °C
Storage Temperature	T _{stg}	-55 to +150 °C

Electrical Characteristics at Ta = 25°C

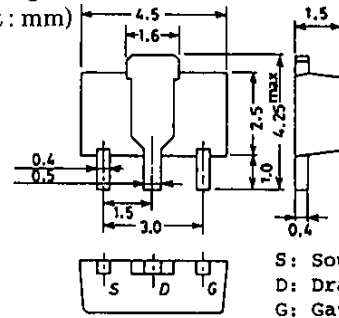
			min	typ	max	unit
D-S Breakdown Voltage	V _{(BR)DSS}	I _D = 1mA, V _{GS} = 0	30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30V, V _{GS} = 0			10	μA
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±12V, V _{DS} = 0			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} = 10V, I _D = 1mA	1.0		2.0	V
Forward Transfer Admittance	Y _{fs}	V _{DS} = 10V, I _D = 500mA	0.6	1.0		S
Static Drain to Source on State Resistance	R _{DSS(on)}	I _D = 500mA, V _{GS} = 10V		0.5	0.75	Ω
	R _{DSS(on)}	I _D = 500mA, V _{GS} = 4V		0.75	1.1	Ω
Input Capacitance	C _{iss}	V _{DS} = 10V, f = 1MHz		50		pF
Output Capacitance	C _{oss}	V _{DS} = 10V, f = 1MHz		35		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} = 10V, f = 1MHz		10		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		5		ns
Rise Time	t _r	∕		10		ns
Turn-OFF Delay Time	t _{d(off)}	∕		30		ns
Fall Time	t _f	∕		20		ns
Diode Forward Voltage	V _{SD}	I _S = 1A, V _{GS} = 0		1.0		V

Switching Time Test Circuit



Package Dimensions 2062

(unit: mm)

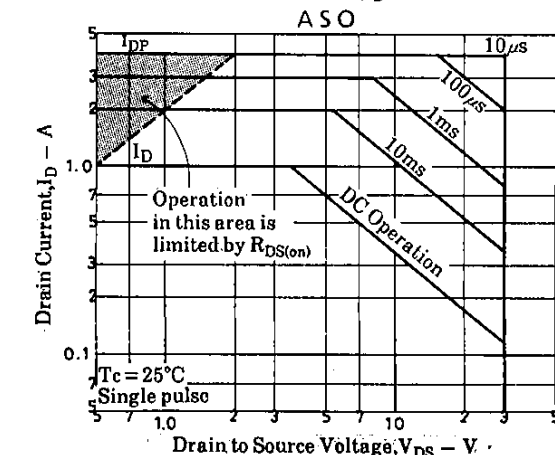
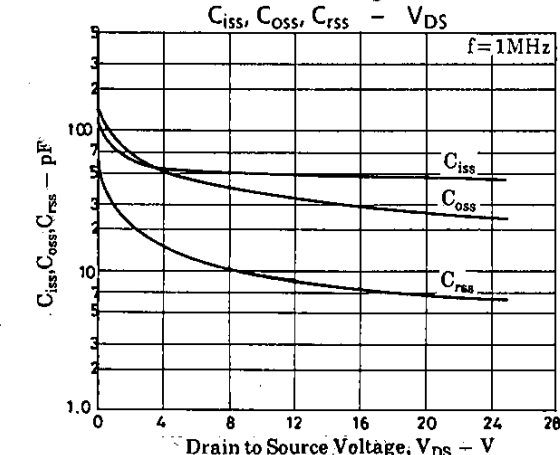
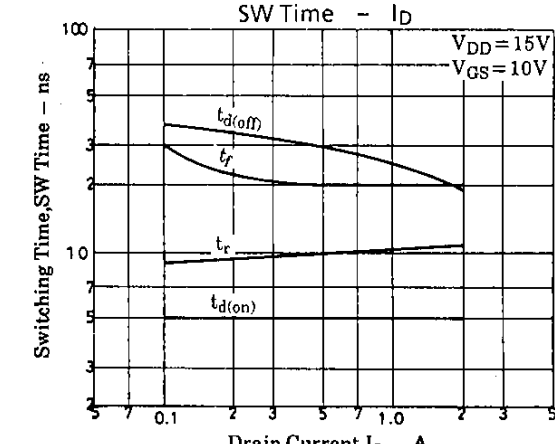
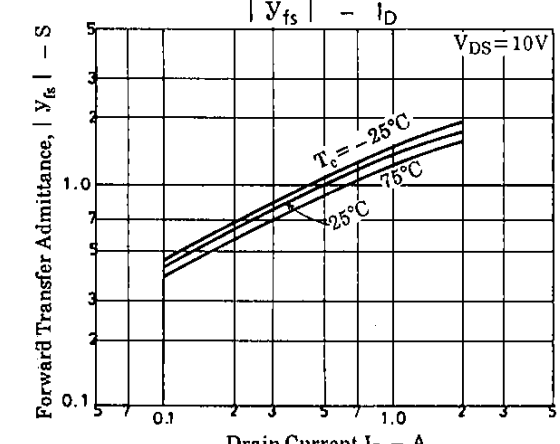
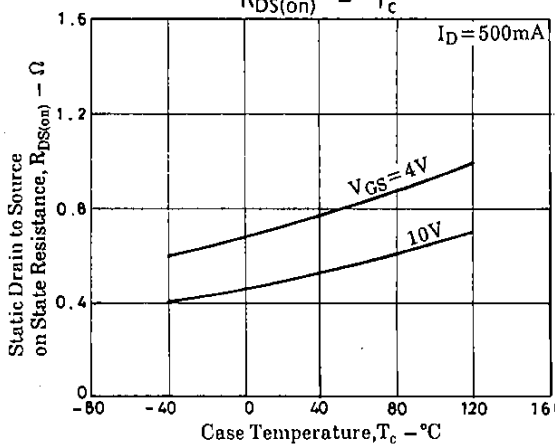
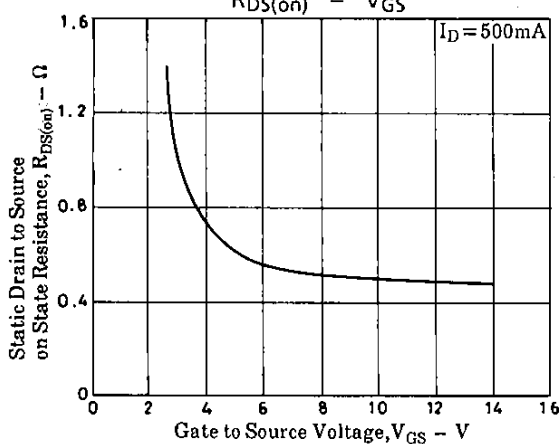
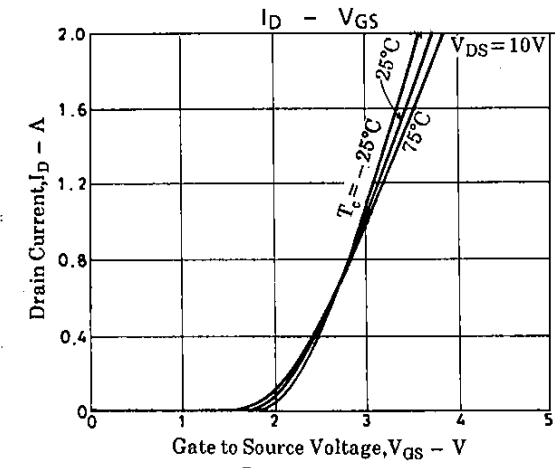
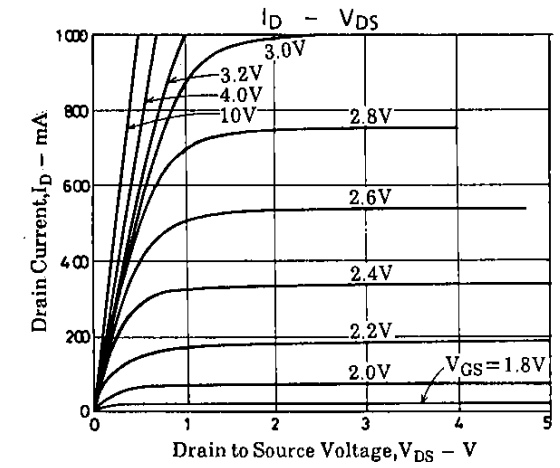


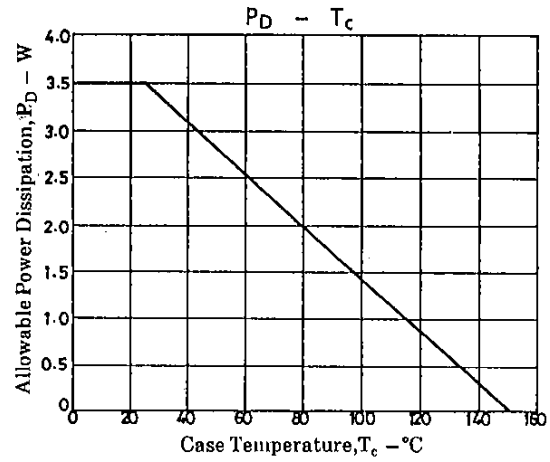
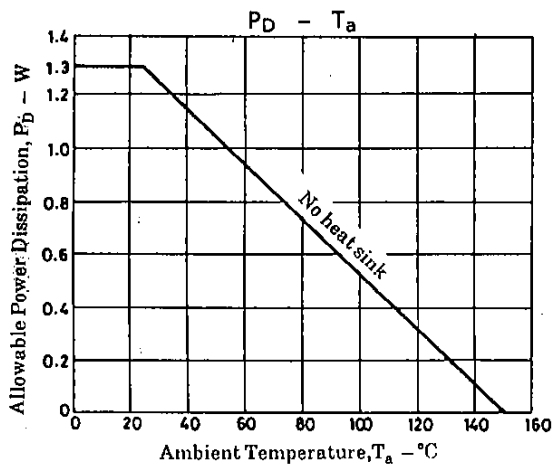
S: Source
D: Drain
G: Gate

SANYO: PCP

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